

P-Channel 80- and 100-V (D-S) MOSFETs

PRODUCT SUMMARY						
Part Number	V _{(BR)DSS} Min (V)	$r_{DS(on)}$ Max (Ω)	V _{GS(th)} (V)	I _D (A)		
VP0808L	-80	5 @ V _{GS} = -10 V	−2 to −4.5	-0.28		
VP1008L	-100	5 @ V _{GS} = -10 V	−2 to −4.5	-0.28		

FEATURES

High-Side Switching
 Low On-Resistance: 2.5 Ω
 Moderate Threshold: -3.4 V
 Fast Switching Speed: 40 ns

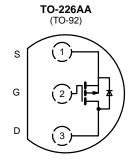
• Low Input Capacitance: 75 pF

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Switching
- Easily Driven Without Buffer

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply, Converter Circuits
- Motor Control



Top View



"S" VP 0808P xxyy

"S" = Siliconix Logo xxyy = Date Code VP1008L

Device Marking
Front View

"S" VP
1008L
xxyy

"S" = Siliconix Logo xxyy = Date Code

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parame	ter	Symbol	VP0808L	VP1008L	Unit		
Drain-Source Voltage		V _{DS}	-80	-100	V		
Gate-Source Voltage		V_{GS}	±30	±30	7 '		
Continuous Drain Current	T _A = 25°C		-0.28	-0.28			
$(T_J = 150^{\circ}C)$	T _A = 100°C	I _D	-0.17	-0.17	Α		
Pulsed Drain Current ^a		I _{DM}	-3	-3	1		
Power Dissipation	T _A = 25°C	Б	0.8	0.8	10/		
	T _A = 100°C	P _D	0.32	0.32	W		
Thermal Resistance, Junction-to-Ambier	t	R_{thJA}	156	156	°C/W		
Operating Junction and Storage Tempera	ature Range	T _J , T _{stg}	-55 t	o 150	°C		

Notes

Pulse width limited by maximum junction temperature.

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
			Typ ^a	Limits				
				VP0808L		VP1	VP1008L	
Parameter	Symbol	Test Conditions		Min	Max	Min	Max	Unit
Static				•				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = -10 \mu\text{A}$	-110	-80		-100		
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -1$ mA	-3.4	-2	-4.5	-2	-4.5	V
0 . 5		V_{DS} = 0 V, V_{GS} = ± 20 V			±100		±100	
Gate-Body Leakage	I _{GSS}	T _J = 125°C			±500		±500	nA
		$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-10			
7 0 . 1		T _J = 125°C			-500			1
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$					-10	μΑ
		T _J = 125°C					-500	1
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}$	-2	-1.1		-1.1		Α
h	r _{DS(on)}	$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$	2.5		5		5	
Drain-Source On-Resistance ^b		T _J = 125°C	4.4		8		8	Ω
Forward Transconductance ^b	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	325	200		200		
Common Source Output Conductance ^b	9 _{os}	$V_{DS} = -7.5 \text{ V}, I_{D} = -0.1 \text{ A}$	0.45					mS
Dynamic				•		•		
Input Capacitance	C _{iss}		75		150		150	pF
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz	40		60		60	
Reverse Transfer Capacitance	C _{rss}	1 - 1 1911 12			25		25	1
Switching ^c				•		•		
Turn-On Time	t _{d(on)}		11		15		15	
	t _r	$V_{DD} = -25 \text{ V, } R_L = 47 \Omega$ $I_D \cong -0.5 \text{ A, } V_{GEN} = -10 \text{ V}$ $R_G = 25 \Omega$	30		40		40	ns
Turn Off Time	t _{d(off)}		20		30		30	
Turn-Off Time	t _f		20		30		30	1

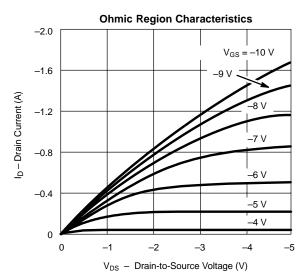
VPDV10

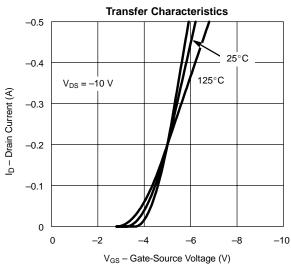
Notes a. For DESIGN AID ONLY, not subject to production testing.. b. Pulse test: $PW \le 300 \ \mu s$ duty cycle $\le 2\%$. c. Switching time is essentially independent of operating temperature.

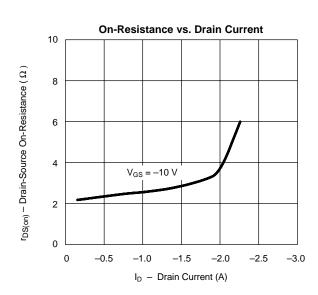


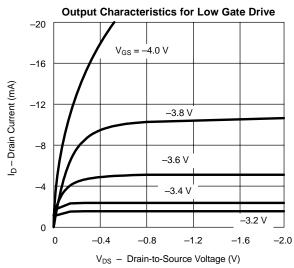
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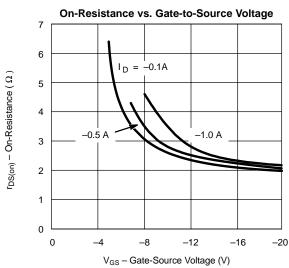
TYPICAL CHARACTERISTICS (TA = 25°C UNLESS OTHERWISE NOTED)

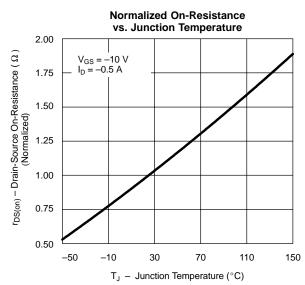








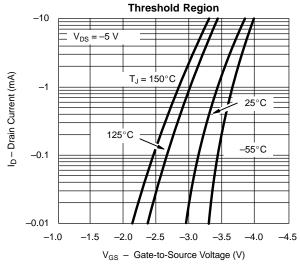


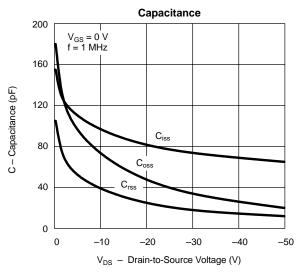


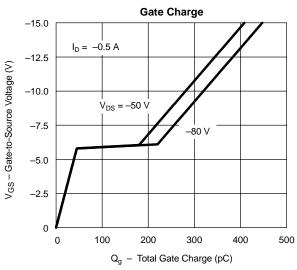
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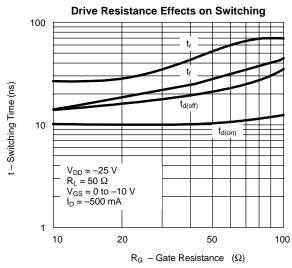


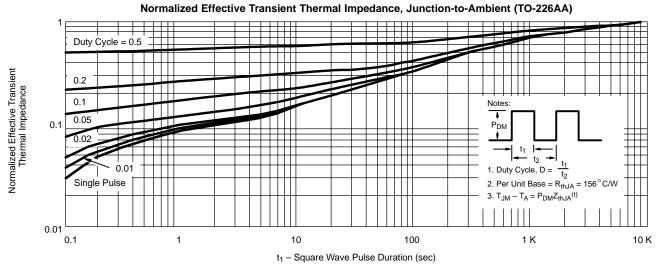
TYPICAL CHARACTERISTICS (TA = 25°C UNLESS OTHERWISE NOTED)













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